



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

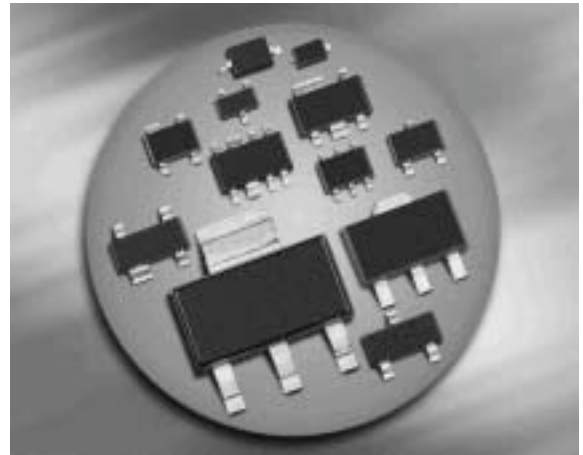
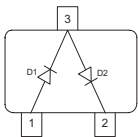
Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



Silicon Switching Diode Array

- For high-speed switching applications
- Pb-free (RoHS compliant) package ¹⁾
- Qualified according AEC Q101


SMBD7000/MMBD7000


Type	Package	Configuration	Marking
SMBD7000/MMBD7000	SOT23	series	s5C

Maximum Ratings at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	100	V
Peak reverse voltage	V_{RM}	100	
Forward current	I_F	200	mA
Non-repetitive peak surge forward current	I_{FSM}		A
$t = 1 \mu\text{s}$		4.5	
$t = 1 \text{ s}$		0.5	
Total power dissipation $T_S \leq 28^\circ\text{C}$	P_{tot}	330	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ²⁾ SMBD7000/MMBD7000	R_{thJS}	≤ 360	K/W

¹Pb-containing package may be available upon special request

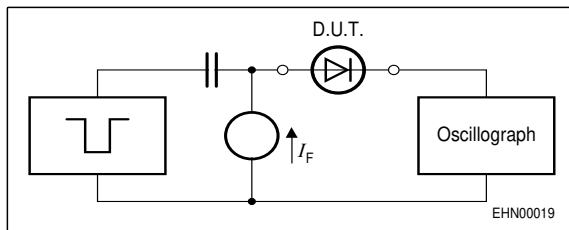
²For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Breakdown voltage $I_{(BR)} = 100 \mu\text{A}$	$V_{(BR)}$	100	-	-	V
Reverse current $V_R = 50 \text{ V}$ $V_R = 100 \text{ V}$ $V_R = 50 \text{ V}, T_A = 150^\circ\text{C}$	I_R	-	-	0.3 0.5 100	μA
Forward voltage $I_F = 1 \text{ mA}$ $I_F = 10 \text{ mA}$ $I_F = 50 \text{ mA}$ $I_F = 100 \text{ mA}$ $I_F = 150 \text{ mA}$	V_F	550 670 - 750 -	- - - - -	700 820 1000 1100 1250	mV

AC Characteristics

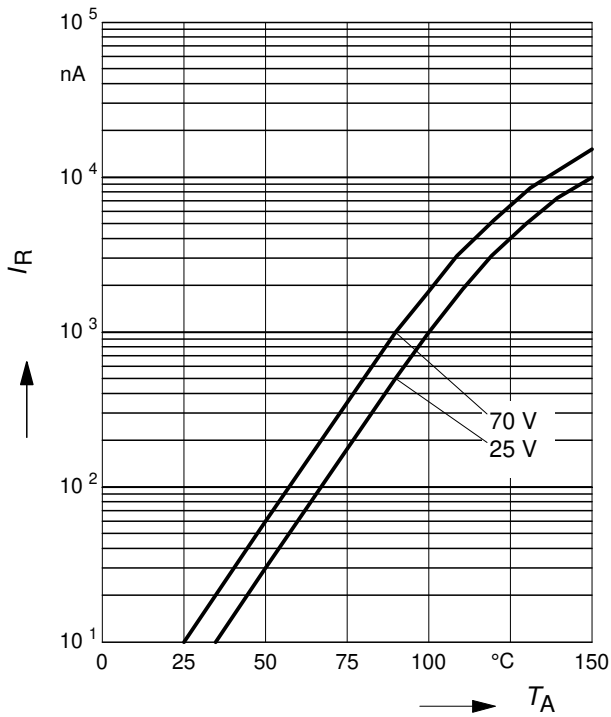
Diode capacitance $V_R = 0 \text{ V}, f = 1 \text{ MHz}$	C_T	-	-	2	pF
Reverse recovery time $I_F = 10 \text{ mA}, I_R = 10 \text{ mA}$, measured at $I_R = 1 \text{ mA}$, $R_L = 100 \Omega$	t_{rr}	-	-	4	ns

Test circuit for reverse recovery time

 Pulse generator: $t_p = 100\text{ns}$, $D = 0.05$, $t_r = 0.6\text{ns}$,
 $R_i = 50\Omega$

 Oscilloscope: $R = 50\Omega$, $t_r = 0.35\text{ns}$, $C \leq 1\text{pF}$

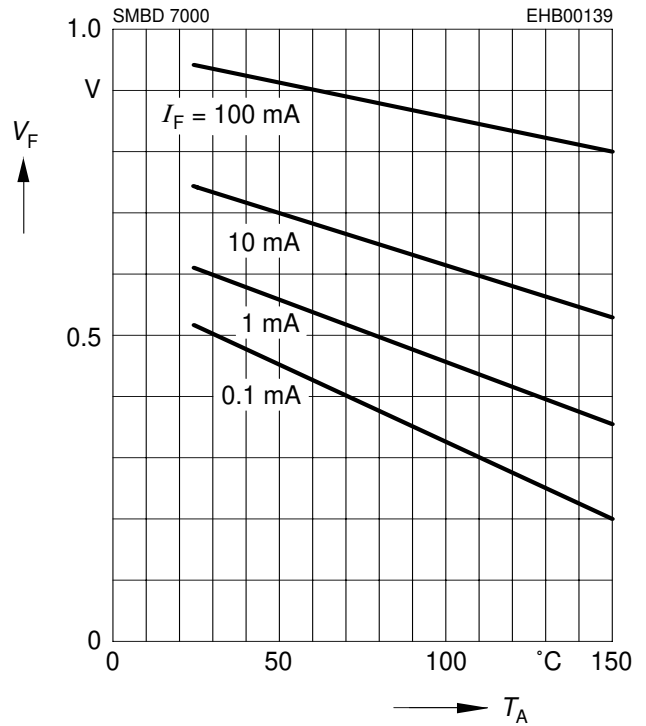
Reverse current $I_R = f(T_A)$

$V_R =$ Parameter



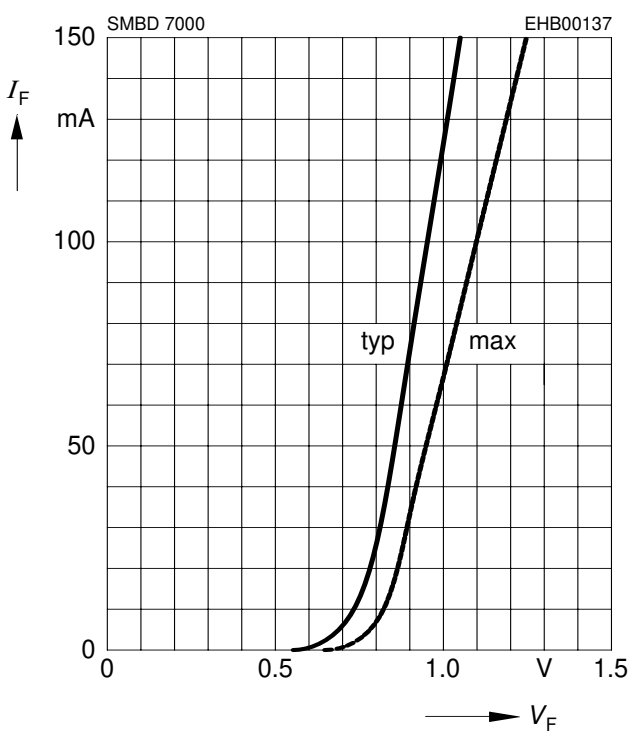
Forward Voltage $V_F = f(T_A)$

$I_F =$ Parameter



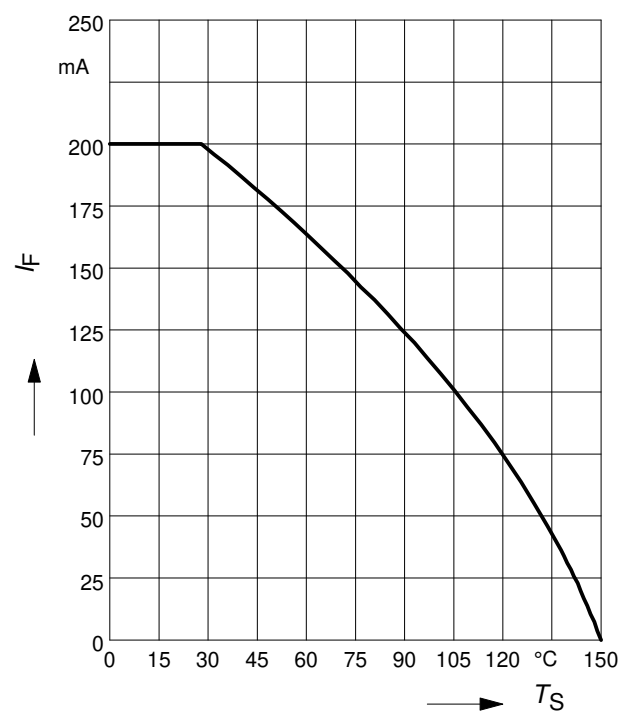
Forward current $I_F = f(V_F)$

$T_A = 25^\circ\text{C}$

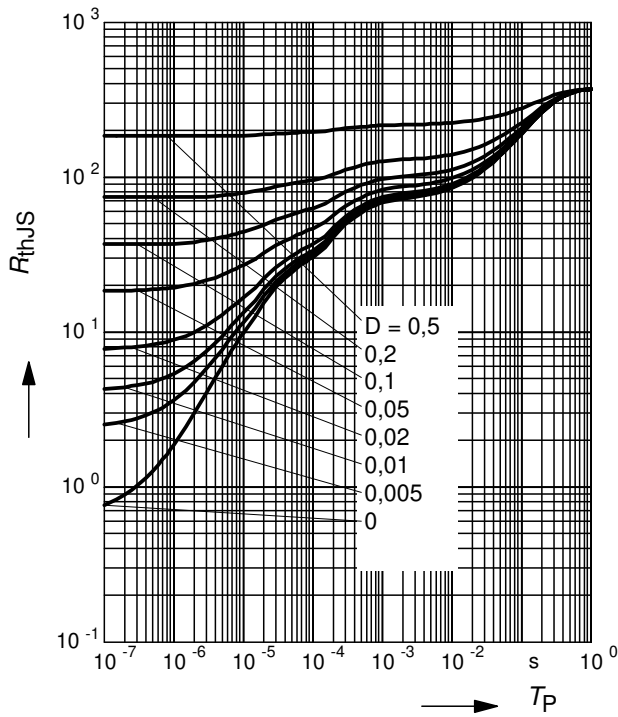


Forward current $I_F = f(T_S)$

SMBD7000/MMBD7000

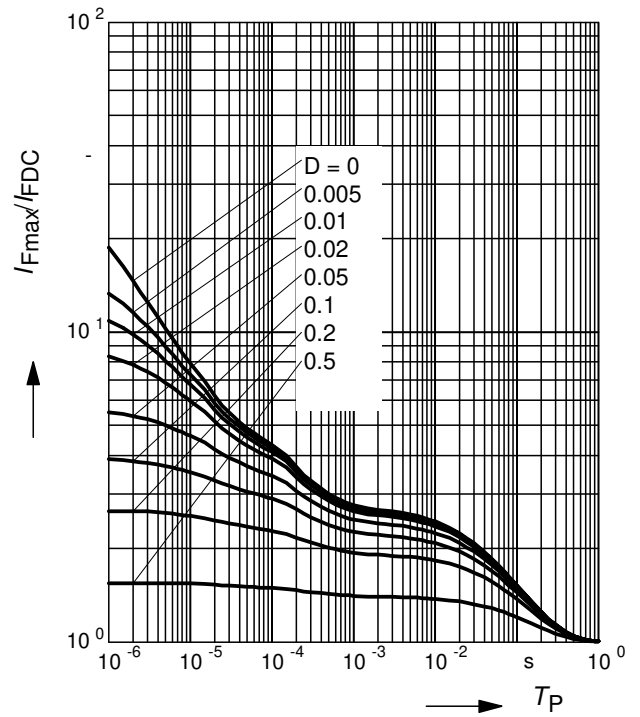


Permissible Puls Load $R_{thJS} = f(t_p)$

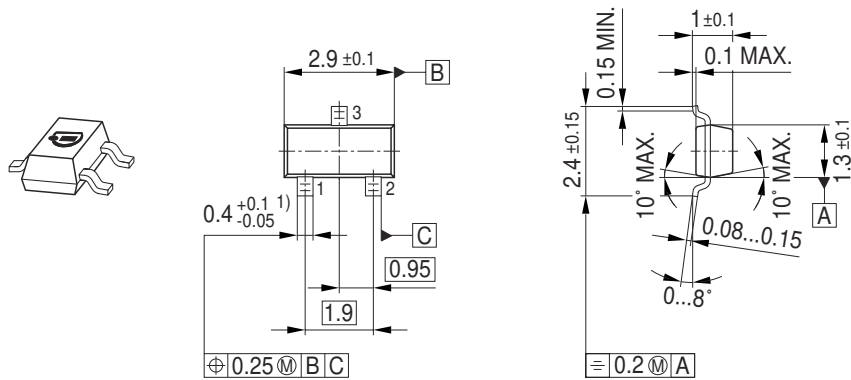


Permissible Pulse Load

$I_{Fmax}/I_{FDC} = f(t_p)$

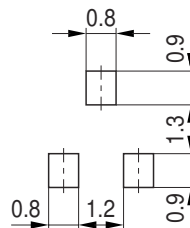


Package Outline

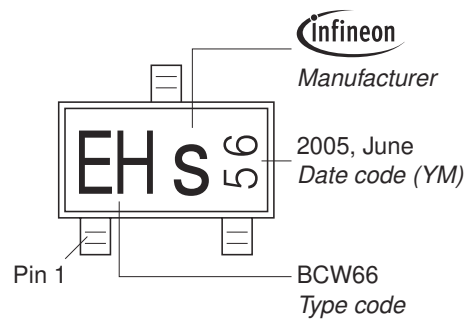


1) Lead width can be 0.6 max. in dambar area

Foot Print

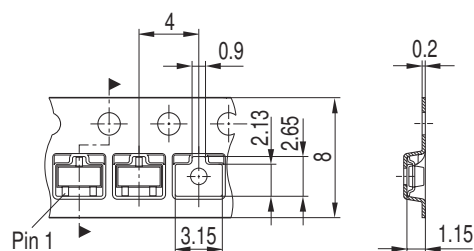


Marking Layout (Example)



Standard Packing

Reel \varnothing 180 mm = 3.000 Pieces/Reel
 Reel \varnothing 330 mm = 10.000 Pieces/Reel



Edition 2006-02-01
Published by
Infineon Technologies AG
81726 München, Germany
© Infineon Technologies AG 2007.
All Rights Reserved.

Attention please!

The information given in this dokument shall in no event be regarded as a guarantee of conditions or characteristics ("Beschaffenheitsgarantie"). With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

Information

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office (www.infineon.com).

Warnings

Due to technical requirements components may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies Office.

Infineon Technologies Components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system.

Life support devices or systems are intended to be implanted in the human body, or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.